

ABSTRACT OF THE DISCLOSURE

The present invention provides a semiconductor device wherein the area of a peripheral circuit region with respect to a pixel region is reduced, and provides a manufacturing method of the semiconductor device. A semiconductor device

5 according to the present invention is characterized by having a pixel region 1, peripheral circuit regions 2a to 2c arranged in at least a part of the periphery of the pixel region, and a wiring formed in the peripheral circuit region, and by having a wiring multilayered with two or more layers. At least one layer of the multilayered wiring is formed from a low resistance material. Transistors are formed in the peripheral circuit
10 region, and the multilayer wiring with two or more layers is formed on the upper side of the transistors.